

This listing of claims replaces all prior versions, and listings of claims in the instant application:

Listing of Claims:

PLEASE CANCEL CLAIMS 1 TO 15, WITHOUT PREJUDICE

16. (Presently Amended) ~~The retirement payload array of Claim 11,~~

A retirement payload array comprised of modified column structures, each of said modified column structures comprising:

a read bit line;

a pre-charge device coupled to said read bit line;

a sensing device coupled to said read bit line;
at least one memory cell, said memory cell comprising an output coupled to said read bit line
and an input;

a gate, said gate comprising an output coupled to said input of said at least one memory cell and an input;

a conditional read circuit, said conditional read circuit comprising a first input, a second input and an output, said conditional read circuit output being coupled to said input of said gate,

a clock signal, said clock signal having a first or "A" phase and a second or "B" phase, said clock signal being coupled to said second input of said conditional read circuit;

an advance pointer signal, said advance pointer signal having a first or inactive phase and a second

or active phase, said second or active phase of said advance pointer signal corresponding to a shift in position of a read pointer, said advance pointer signal being coupled to said first input of said conditional read circuit, wherein;

 said conditional read circuit initiates a read of said retirement payload array only when, both:

 said clock signal is in said "B" phase; and
 said advance pointer signal is in said active phase wherein; :

 said gate is a NOR-Gate comprising a first input, a second input and an output, further wherein;

 said conditional read circuit comprises:

 an inverter, said inverter having an input and an output; and

 a NAND-Gate having a first input, a second input, and an output, wherein;

 said inverter input is coupled to said clock signal and said inverter output is coupled to said NAND-Gate second input, further wherein;

 said NAND-Gate first input is coupled to said advance pointer signal and said NAND-Gate output is coupled to said NOR-Gate first input.

PLEASE CANCEL CLAIMS 17 TO 20, WITHOUT PREJUDICE

21. (Previously Presented) A retirement payload array comprised of modified column structures, each of said modified column structures comprising:

 a read bit line;

a pre-charge device coupled to said read bit line, said pre-charge device comprising a transistor;

a sensing device coupled to said read bit line, said sensing device comprising a latch;

at least one memory cell, said memory cell comprising an output coupled to said read bit line and an input;

a NOR-Gate comprising a first input, a second input and an output, said NOR-Gate output being coupled to said input of said at least one memory cell;

a conditional read circuit, said conditional read circuit comprising:

an inverter, said inverter having an input and an output; and

a NAND-Gate having a first input, a second input, and an output, said NAND-Gate output being coupled to said NOR-Gate first input, said inverter output being coupled to said NAND-Gate second input;

a clock signal, said clock signal having a first or "A" phase and a second or "B" phase, said clock signal being coupled to said input of said inverter of said conditional read circuit, said pre-charge devices being pre-charged when said clock signal is in said first or "A" phase;

an advance pointer signal, said advance pointer signal having a first or inactive phase and a second or active phase, said second or active phase of said advance pointer signal corresponding to a shift in position of a read pointer, said advance pointer signal being coupled to said first input of said NAND-Gate of said conditional read circuit, wherein;

said conditional read circuit initiates a read of said retirement payload array only when, both:

said clock signal is in said "B" phase; and
 said advance pointer signal is in said active
phase.

22. (Presently Amended) The retirement payload array of Claim 21, wherein~~r~~ :
 said retirement payload array comprises M rows of memory cells and N of said column structures.

23. (Presently Amended) The retirement payload array of Claim 22, wherein~~r~~ :
 said retirement payload array comprises M read word lines and N read bit lines, further wherein;
 each of said N read bit lines is coupled to a corresponding pre-charge device and a corresponding sensing device.

24. (Presently Amended) The method of Claim 21, wherein~~r~~ :
 said retirement payload array is a 192 column, 16-read word line register file structure employing a dynamic, full swing pull down read mechanism.